

### Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on  $V_F$
- Temperature Independent Switching Behavior
- High surge current capability

$V_R = 650\text{ V}$   
 $I_F = 10\text{ A (}T_C=140^\circ\text{C)}$   
 $Q_C = 23\text{ nC (}V_R=400\text{ V)}$

### Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

DFN 8x8



### Applications

- PC Power
- Server Power Supply
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

### Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$		650	V
Peak Reverse Surge Voltage	$V_{RSM}$		650	V
DC Blocking Voltage	$V_R$		650	V
Continuous Forward Current	$I_F$	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=140^\circ\text{C}$	28 11 10	A
Non repetitive Forward Surge Current	$I_{FSM}$	$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Pulse $T_C = 110^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Pulse $T_C = 25^\circ\text{C}$ , $t_p=10\ \mu\text{s}$ , Square	50 40 300	A
Repetitive peak Forward Surge Current	$I_{FRM}$	$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_C = 110^\circ\text{C}$ , $t_p=10\text{ ms}$ , Freq = 0.1Hz, 100 cycles, Half Sine Pulse	40 30	A
Total power dissipation	$P_D$	$T_C=25^\circ\text{C}$	83	W
Operating Junction Temperature	$T_J$		-55 to 175	$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 to 175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	$V_{DC}$	$I_R = 250\mu A, T_J = 25^\circ C$	650			V
Forward Voltage	$V_F$	$I_F = 10A, T_J = 25^\circ C$		1.5	1.8	V
		$I_F = 10A, T_J = 125^\circ C$		1.65		
		$I_F = 10A, T_J = 175^\circ C$		1.8		V
Reverse Current	$I_R$	$V_R = 650V, T_J = 25^\circ C$		10	80	$\mu A$
		$V_R = 650V, T_J = 125^\circ C$		68		$\mu A$
		$V_R = 650V, T_J = 175^\circ C$		190		$\mu A$
Total Capacitive Charge	$Q_C$	$V_R = 400V$ $T_J = 25^\circ C$		23		nC
Total Capacitance	C	$V_R = 1V, T_J = 25^\circ C,$ Freq = 1MHz		387		pF
		$V_R = 200V, T_J = 25^\circ C,$ Freq = 1MHz		48		
		$V_R = 400V, T_J = 25^\circ C,$ Freq = 1MHz		33		

Note: This is a majority carrier diode, so there is no reverse recovery charge

## Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	junction-case		1.8		$^\circ C/W$

### Typical Electrical Curves

Figure 1. Forward Characteristics

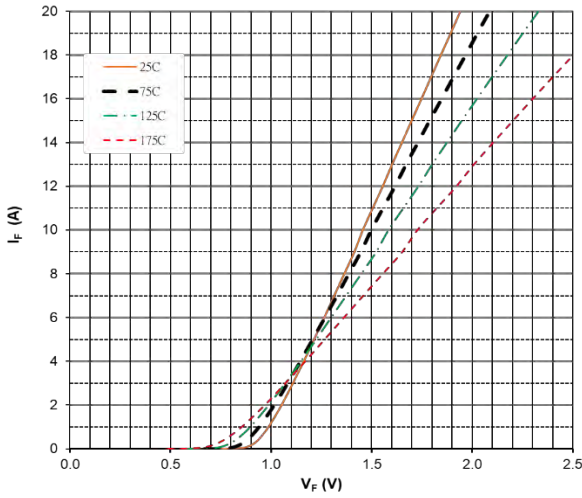


Figure 2. Forward Characteristics

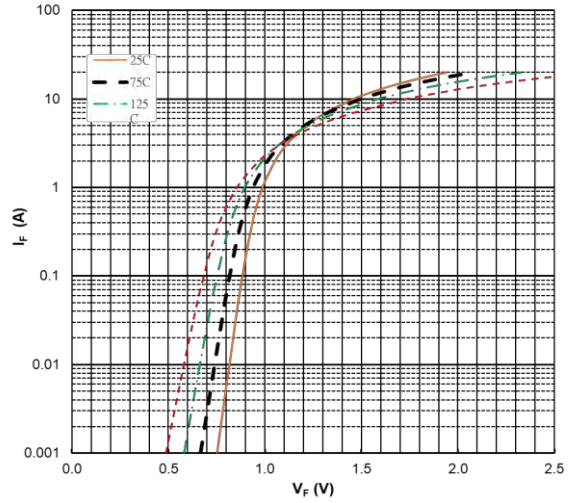


Figure 3. Reverse Characteristics

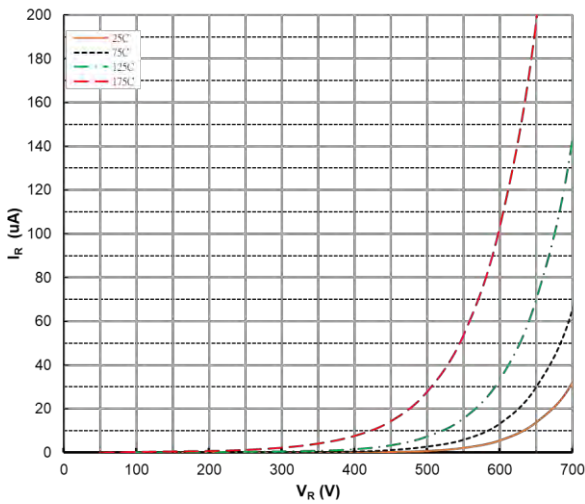


Figure 4. Power Derating

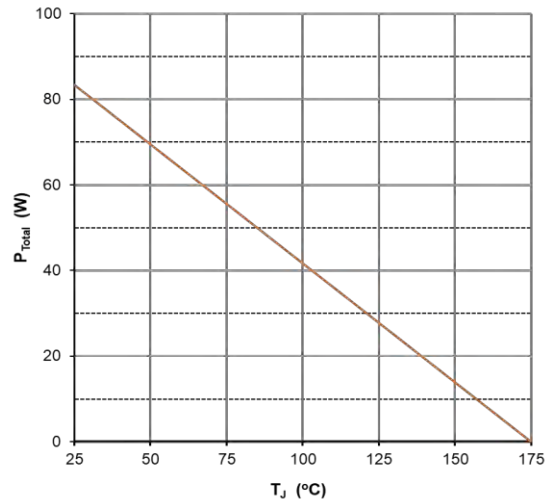


Figure 5. Capacitance vs Reverse Voltage

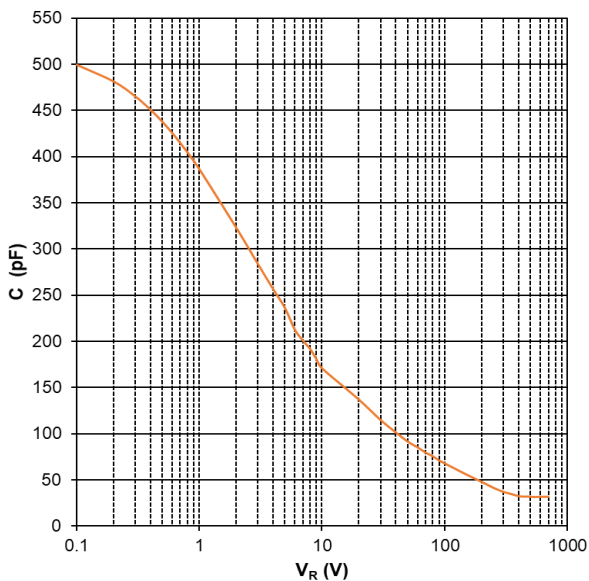
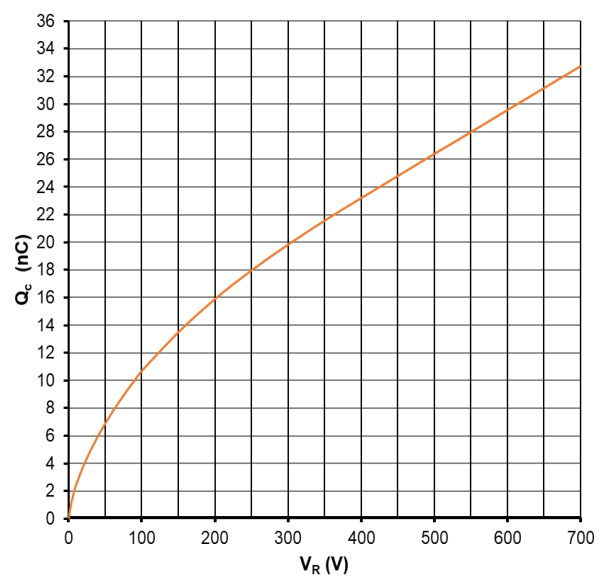
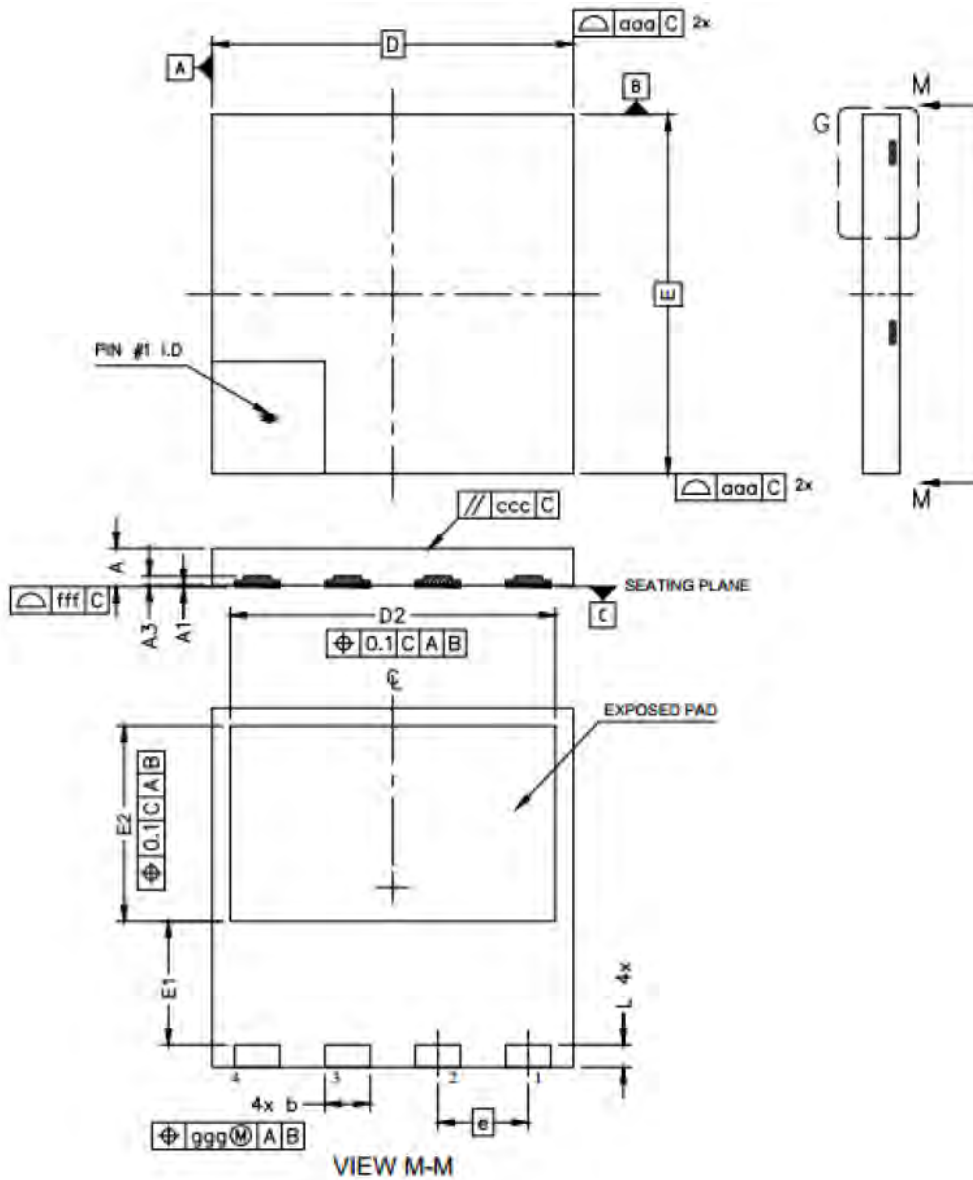


Figure 6. Recovery Charge vs Reverse Voltage



## Package Dimensions

(DFN 8x8 Package)



Items	Millimeters	
	Min	Max
A	0.75	0.95
A1	0.00	0.05
A3	0.10	0.30
b	0.9	1.10
D	7.90	8.10
E	7.90	8.10
D2	7.10	7.30
E1	2.65	2.85
E2	4.25	4.45
e	2.00 (BSC)	
L	0.40	0.60
aaa	0.10	
ggg	0.05	
ccc	0.05	
fff	0.05	

### Ordering Information

Part Number	Package	Packing	Marking	Base Quantity
LGE3D10065G	DFN 8x8	3000pcs / Tape & Reel	LGE3D10065G	3000